

CBR1U-D010S
CBR1U-D020S

**SURFACE MOUNT
1 AMP ULTRA FAST
SILICON BRIDGE RECTIFIER**

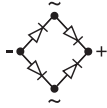
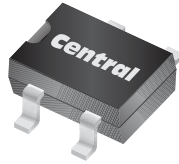


www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1U-D010S, CBR1U-D020S types are silicon full wave ultra fast bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER



SMDIP CASE

MAXIMUM RATINGS:

($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	CBR1U-D010S	CBR1U-D020S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	V
DC Blocking Voltage	V_R	100	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	V
Average Forward Current ($T_A=40^{\circ}\text{C}$)	I_O		1.0	A
Peak Forward Surge Current	I_{FSM}		50	A
Operating and Storage				
Junction Temperature	T_J, T_{stg}	-65 to +150		$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	40		$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

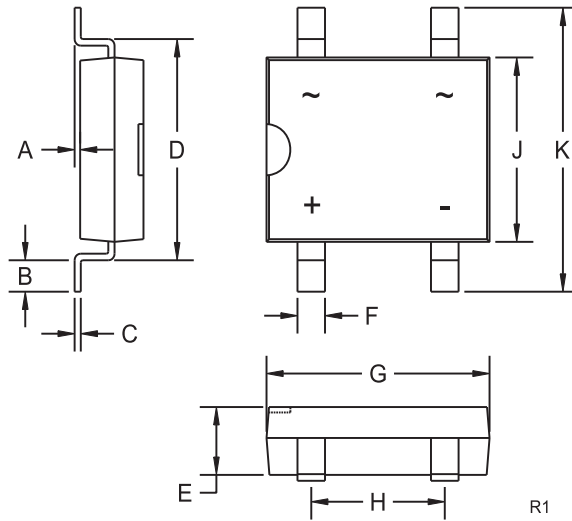
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R =Rated V_{RRM}		5.0	μA
I_R	V_R =Rated V_{RRM} , $T_A=125^{\circ}\text{C}$		1.0	mA
V_F	$I_F=1.0\text{A}$		1.05	V
t_{rr}	$I_F=500\text{mA}$, $I_R=1.0\text{A}$, $I_{rr}=250\text{mA}$		50	ns

CBR1U-D010S
CBR1U-D020S

SURFACE MOUNT
1 AMP ULTRA FAST
SILICON BRIDGE RECTIFIER



SMDIP CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R3 (4-January 2010)